

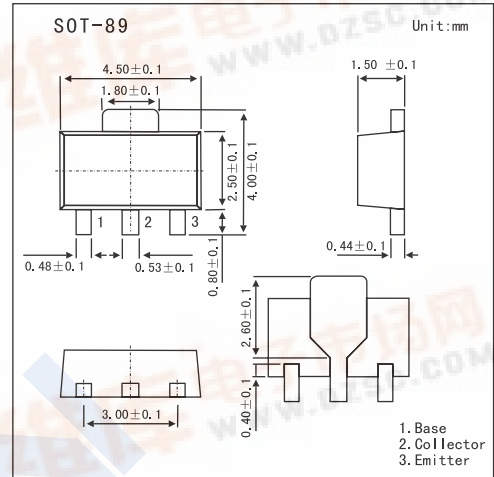
SMD Type Transistors

Power Switching Applications

2SA1213

Features

- Low Saturation Voltage: $V_{CE(sat)} = -0.5V$ (max) ($I_C = -1A$)
- High Speed Switching Time: $t_{stg} = 1.0\mu s$ (typ.)
- Small Flat Package
- $P_C = 1$ to $2W$ (mounted on ceramic substrate)
- Complementary to 2SC2873



Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-2	A
Base Current	I_B	-0.4	A
Collector Power Dissipation	P_C	500	mW
	P_{C^*}	1000	
Junction temperature	T_j	150	$^\circ C$
Storage temperature Range	T_{stg}	-55 to +150	$^\circ C$

* Mounted on ceramic substrate (250 mm² x 0.8 t)

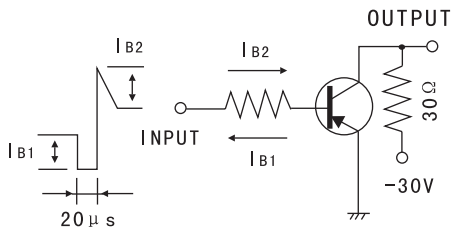
Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-50			V
DC Current Gain	h_{FE}	$V_{CE} = -2V, I_C = -0.5A$	70		240	
		$V_{CE} = -2V, I_C = -2.0A$	20			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -0.05A$			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -1A, I_B = -0.05A$			-1.2	V
Transition Frequency	f_T	$V_{CE} = -2V, I_C = -0.5A$		120		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		40		pF
Turn-On Time	t_{on}	See Test Circuit.		0.1		μs
Storage Time	t_{stg}			1.0		
	t_r			0.1		



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Test Circuit

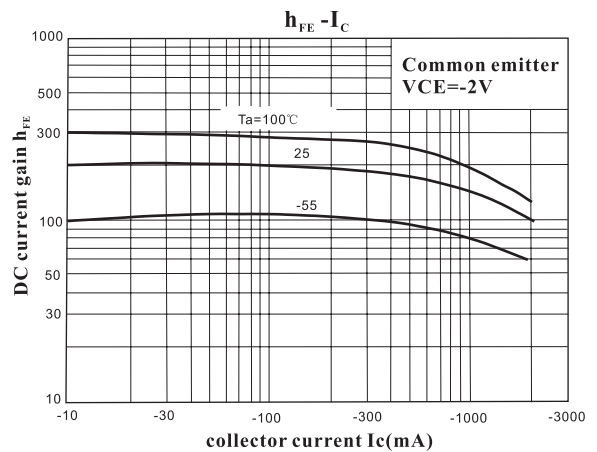
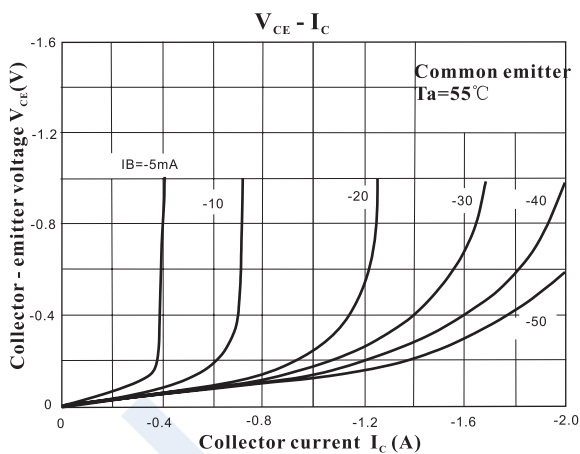
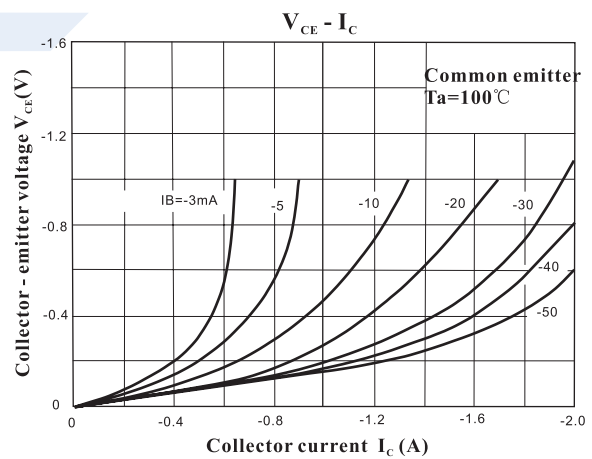
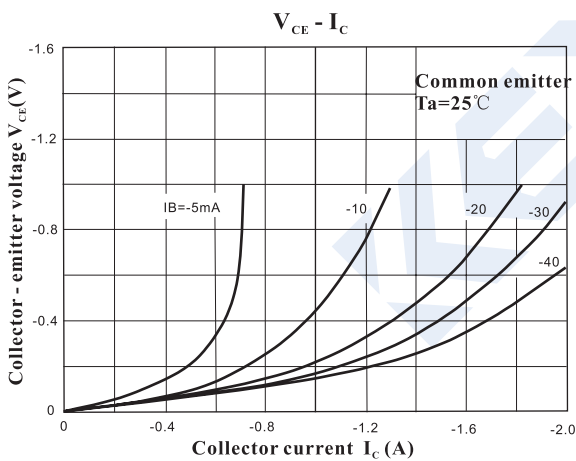


$$-I_{B1} = I_{B2} = 0.05A, \text{ DUTY CYCLE} \leq 1\%$$

hFE Classification

Marking	N	
Rank	O	Y
hFE	70 ~ 140	120 ~ 240

Electrical Characteristics Curves



2SA1213

